

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No. .... 6878507 B2  
Patent Issue Date ..... April 12, 2005  
Application Serial No. .... 09885393  
Filing Date ..... June 19, 2001  
Assignee ..... Micron Technology, Inc.  
Inventorship ..... Richard Holscher et al.  
Attorney's Docket No. .... MI22-1694  
Title: ..... Semiconductor Processing Methods

**REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT**  
**FOR PTO MISTAKE (37 C.F.R. 1.322(a))**

To: Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

ATTN: Decision and Certificate of Correction  
Branch of the Patent Issue Division

From: Robert C. Hyta (Tel. 509-624-4276; Fax 509-838-3424)  
Wells St. John P.S.  
601 W. First Avenue, Suite 1300  
Spokane, WA 99201-3828

Sir/Madam:

It is hereby requested that a Certificate of Correction be issued with respect to US 6878507 B2, granted April 12, 2005, in accordance with the Certificate of Correction form attached hereto.

The errors listed on the Certificate of Correction form were apparently incurred through the fault of the PTO as will be disclosed by the records of files in the Office.

Attached hereto is Form PTO-1050, which is suitable for printing.

Since this Certificate of Correction is being requested due to PTO errors, it is believed that no fee is due. However, in the event that a fee is required for issuance of this Certificate of Correction, please charge the fee specified under 37 C.F.R. § 1.20(a) to Deposit Account No. 23-0925. Please credit Deposit Account No. 23-0925 with any overpayment of the above fee.

Respectfully submitted,

Dated: 1/31/08

By: 

Robert C. Hyta  
Reg. No. 46,791

UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION

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PATENT NO. : 6878507B2

APPLICATION NO.: 09885393

DATED : April 12, 2005

INVENTOR(S) : Holscher, Richard D.; Yin, Zhiping;  
Glass, Thomas R.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Pg. 3, col. 2, - Other Publications

Insert --Abstract: Loboda, M. et al., "Using Trimethylsilane to Improve Safety, Throughput and Versatility in PECVD Processes", Electrochemical Society Mtg., #358, Montreal, Quebec, Vol. MA 97-1, 1997, pg. 454--

Pg. 3, col. 2, - Other Publications

Insert --Julius Grant, "Hack's Chemical Dictionary", McGraw-Hill Book Co., 1969, Fourth Ed., pg. 27--

Col. 2, line 64-

Replace "oxygen, about 10% to about 35% is"  
With --oxygen, about 10% to about 35%--

Col. 3, line 29 -

Replace "about 400° C. (preferably greater than 400 °C., prior to"  
With --about 400° C. (preferably greater than 400 °C.) prior to--

**Mailing Address of Sender:**

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